Jean Christophe Harmand

List of Publications by Year
in descending order

#	Article	IF	Citations
1	Why Does Wurtzite Form in Nanowires of III-V Zinc Blende Semiconductors?. Physical Review Letters, 2007, 99, 146101.	7.8	669
2	Growth kinetics and crystal structure of semiconductor nanowires. Physical Review B, 2008, 78, .	3.2	276
3	Analysis of vapor-liquid-solid mechanism in Au-assisted GaAs nanowire growth. Applied Physics Letters, 2005, 87, 203101.	3.3	249
4	Crystal Phase Quantum Dots. Nano Letters, 2010, 10, 1198-1201.	9.1	233
5	Theoretical analysis of the vapor-liquid-solid mechanism of nanowire growth during molecular beam epitaxy. Physical Review E, 2006, 73, 021603.	2.1	163
6	Predictive modeling of self-catalyzed III-V nanowire growth. Physical Review B, 2013, 88, .	3.2	158
7	Au-assisted molecular beam epitaxy of InAs nanowires: Growth and theoretical analysis. Journal of Applied Physics, 2007, 102, 094313.	2.5	136
8	Arsenic Pathways in Self-Catalyzed Growth of GaAs Nanowires. Crystal Growth and Design, 2013, 13, 91-96.	3.0	133
9	New Mode of Vaporâ˘'Liquidâ˘'Solid Nanowire Growth. Nano Letters, 2011, 11, 1247-1253.	9.1	132
10	Critical diameters and temperature domains for MBE growth of IIIâ€"V nanowires on lattice mismatched substrates. Physica Status Solidi - Rapid Research Letters, 2009, 3, 112-114.	2.4	116
11	Epitaxy of GaN Nanowires on Graphene. Nano Letters, 2016, 16, 4895-4902.	9.1	115
12	Atomic Step Flow on a Nanofacet. Physical Review Letters, 2018, 121, 166101.	7.8	113
13	Temperature-dependent valence band offset and band-gap energies of pseudomorphic GaAsSb on GaAs. Journal of Applied Physics, 2001, 89, 5473-5477.	2.5	112
14	Growth and Characterization of InP Nanowires with InAsP Insertions. Nano Letters, 2007, 7, 1500-1504.	9.1	110
15	Growth of GaN free-standing nanowires by plasma-assisted molecular beam epitaxy: structural and optical characterization. Nanotechnology, 2007, 18, 385306.	2.6	109
16	Temperature conditions for GaAs nanowire formation by Au-assisted molecular beam epitaxy. Nanotechnology, 2006, 17, 4025-4030.	2.6	107
17	Comparison of nitrogen incorporation in molecular-beam epitaxy of GaAsN, GaInAsN, and GaAsSbN. Applied Physics Letters, 2000, 77, 2482-2484.	3.3	106
18	Nucleation Antibunching in Catalyst-Assisted Nanowire Growth. Physical Review Letters, 2010, 104, 135501.	7.8	100

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19	Room-temperature defect-engineered spin filter based on a non-magnetic semiconductor. Nature Materials, 2009, 8, 198-202.	27.5	94
20	GaNAsSb: how does it compare with other dilute IIIÂV-nitride alloys?. Semiconductor Science and Technology, 2002, 17, 778-784.	2.0	93
21	GaAsSbN: a new low-bandgap material for GaAs substrates. Electronics Letters, 1999, 35, 1246.	1.0	90
22	Role of nonlinear effects in nanowire growth and crystal phase. Physical Review B, 2009, 80, .	3.2	90
23	Growth kinetics of a single<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mtext>InP</mml:mtext><mml:mrow><mml:mn>1</mml:mn><mml:mo>â^'</mml:mo><mml:mi>x</ Physical Review B, 2010, 81, .	3.2	83
24	Phase Selection in Self-catalyzed GaAs Nanowires. Nano Letters, 2020, 20, 1669-1675.	9.1	83
25	Facet and in-plane crystallographic orientations of GaN nanowires grown on Si(111). Nanotechnology, 2008, 19, 155704.	2.6	82
26	Record Pure Zincblende Phase in GaAs Nanowires down to 5 nm in Radius. Nano Letters, 2014, 14, 3938-3944.	9.1	82
27	GaInAs/GaAs quantum-well growth assisted by Sb surfactant: Toward 1.3â€‚Î¼m emission. Applied Physics Letters, 2004, 84, 3981-3983.	3.3	81
28	Wide InP Nanowires with Wurtzite/Zincblende Superlattice Segments Are Type-II whereas Narrower Nanowires Become Type-I: An Atomistic Pseudopotential Calculation. Nano Letters, 2010, 10, 4055-4060.	9.1	76
29	High-quality InxGa1â^'xAs/InAlAs modulation-doped heterostructures grown lattice-mismatched on GaAs substrates. Journal of Crystal Growth, 1991, 111, 313-317.	1.5	74
30	Silicon nanowires: Diameter dependence of growth rate and delay in growth. Applied Physics Letters, 2010, 96, .	3.3	64
31	Wurtzite to Zinc Blende Phase Transition in GaAs Nanowires Induced by Epitaxial Burying. Nano Letters, 2008, 8, 1638-1643.	9.1	63
32	Sharpening the Interfaces of Axial Heterostructures in Self-Catalyzed AlGaAs Nanowires: Experiment and Theory. Nano Letters, 2016, 16, 1917-1924.	9.1	60
33	Shape modification of III-V nanowires: The role of nucleation on sidewalls. Physical Review E, 2008, 77, 031606.	2.1	59
34	Morphology of self-catalyzed GaN nanowires and chronology of their formation by molecular beam epitaxy. Nanotechnology, 2011, 22, 245606.	2.6	59
35	Second-harmonic generation in a doubly resonant semiconductor microcavity. Optics Letters, 1997, 22, 1775.	3.3	57
36	Diffusion-controlled growth of semiconductor nanowires: Vapor pressure versus high vacuum deposition. Surface Science, 2007, 601, 4395-4401.	1.9	57

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37	Measuring and Modeling the Growth Dynamics of Self-Catalyzed GaP Nanowire Arrays. Nano Letters, 2018, 18, 701-708.	9.1	55
38	N-Polar GaN Nanowires Seeded by Al Droplets on Si(111). Crystal Growth and Design, 2012, 12, 2724-2729.	3.0	54
39	Zinc blende GaAsSb nanowires grown by molecular beam epitaxy. Nanotechnology, 2008, 19, 275605.	2.6	53
40	Effect of temperature on the optical properties of GaAsSbN/GaAs single quantum wells grown by molecular-beam epitaxy. Journal of Applied Physics, 2003, 93, 4475-4479.	2.5	52
41	Investigations on GaInNAsSb quinary alloy for 1.5 Î¼m laser emission on GaAs. Applied Physics Letters, 2003, 83, 1298-1300.	3.3	50
42	Photoreflectance investigations of the energy level structure in GaInNAs-based quantum wells. Journal of Physics Condensed Matter, 2004, 16, S3071-S3094.	1.8	50
43	Piezo-generator integrating a vertical array of GaN nanowires. Nanotechnology, 2016, 27, 325403.	2.6	50
44	Role of nitrogen in the mobility drop of electrons in modulation-doped GaAsN/AlGaAs heterostructures. Solid State Communications, 2003, 126, 333-337.	1.9	49
45	Morphology and composition of highly strained InGaAs and InGaAsN layers grown on GaAs substrate. Applied Physics Letters, 2004, 84, 203-205.	3.3	49
46	Influence of shadow effect on the growth and shape of InAs nanowires. Journal of Applied Physics, 2012, 111, .	2.5	49
47	Photoreflectance, photoluminescence, and microphotoluminescence study of optical transitions between delocalized and localized states in GaN<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mrow><mml:mn>0.02</mml:mn></mml:mrow></mml:msub></mml:math>As<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mrow><mml:mn>0.98</mml:mn></mml:mrow></mml:msub></mml:math>, Ga<mml:math xmlns:m	3.2	49
48	The role of surface diffusion of adatoms in the formation of nanowire crystals. Semiconductors, 2006, 40, 1075-1082.	0.5	48
49	Abrupt GaP/GaAs Interfaces in Self-Catalyzed Nanowires. Nano Letters, 2015, 15, 6036-6041.	9.1	47
50	Observation of Bloch conduction perpendicular to interfaces in a superlattice bipolar transistor. Applied Physics Letters, 1986, 49, 1260-1262.	3.3	46
51	Lattice-Mismatched Growth and Transport Properties of InAlAs/InGaAs Heterostructures on GaAs Substrates. Japanese Journal of Applied Physics, 1989, 28, L1101-L1103.	1.5	43
52	Electroabsorption modulators for high-bit-rate optical communications: a comparison of strained InGaAs/InAlAs and InGaAsP/InGaAsP MQW. Semiconductor Science and Technology, 1995, 10, 887-901.	2.0	43
53	Spin dynamics in dilute nitride semiconductors at room temperature. Applied Physics Letters, 2005, 87, 252115.	3.3	43
54	Thermal optimization of 1.55Âμm OP-VECSEL with hybrid metalâ€"metamorphic mirror for single-mode high power operation. Optical and Quantum Electronics, 2008, 40, 155-165.	3.3	43

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55	Effect of nitrogen and temperature on the electronic band structure of GaAs1â^'xNx alloys. Applied Physics Letters, 2002, 80, 2075-2077.	3.3	40
56	Photoluminescence characteristics of GaAsSbN/GaAs epilayers lattice-matched to GaAs substrates. Solid State Communications, 2004, 132, 707-711.	1.9	37
57	Photon Cascade from a Single Crystal Phase Nanowire Quantum Dot. Nano Letters, 2016, 16, 1081-1085.	9.1	37
58	Photoreflectance investigations of oscillator strength and broadening of optical transitions for GaAsSbâ€"GaInAs/GaAs bilayer quantum wells. Applied Physics Letters, 2004, 84, 3453-3455.	3.3	36
59	Quantum-well saturable absorber at 1.55Î¼m on GaAs substrate with a fast recombination rate. Applied Physics Letters, 2006, 88, 201110.	3.3	36
60	Influence of carrier localization on modulation mechanism in photoreflectance of GaAsN and GaInAsN. Applied Physics Letters, 2003, 83, 1379-1381.	3.3	35
61	Determination of n-Type Doping Level in Single GaAs Nanowires by Cathodoluminescence. Nano Letters, 2017, 17, 6667-6675.	9.1	35
62	Comparison of light- and heavy-ion-irradiated quantum-wells for use as ultrafast saturable absorbers. Applied Physics Letters, 2001, 79, 2722-2724.	3.3	34
63	Wurtzite GaAs/AlGaAs coreâ€"shell nanowires grown by molecular beam epitaxy. Nanotechnology, 2009, 20, 415701.	2.6	34
64	Electrical and optical characteristics of n-type-doped distributed Bragg mirrors on InP. IEEE Photonics Technology Letters, 1998, 10, 763-765.	2.5	33
65	Ultrafast saturable absorption at 1.55 Î¼m in heavy-ion-irradiated quantum-well vertical cavity. Applied Physics Letters, 2000, 76, 1371-1373.	3.3	33
66	Self-induced growth of vertical GaN nanowires on silica. Nanotechnology, 2016, 27, 135602.	2.6	33
67	Calculation of the temperature profile in nanowhiskers growing on a hot substrate. Physical Review B, 2006, 73, .	3.2	32
68	Investigation of the electronic transport in GaN nanowires containing GaN/AlN quantum discs. Nanotechnology, 2010, 21, 425206.	2.6	31
69	Growth of Vertical GaAs Nanowires on an Amorphous Substrate via a Fiber-Textured Si Platform. Nano Letters, 2013, 13, 2743-2747.	9.1	31
70	Optical polarization relaxation inInxGa1â^'xAs-based quantum wells: Evidence of the interface symmetry-reduction effect. Physical Review B, 1998, 58, R10179-R10182.	3.2	30
71	Experimental investigation of the CMN matrix element in the band anticrossing model for GaAsN and GaInAsN layers. Solid State Communications, 2004, 129, 353-357.	1.9	30
72	Conduction band structure in wurtzite GaAs nanowires: A resonant Raman scattering study. Applied Physics Letters, 2012, 100, .	3.3	30

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73	Investigation of recombination processes involving defect-related states in (Ga,In)(As,Sb,N) compounds. EPJ Applied Physics, 2004, 27, 313-316.	0.7	29
74	Energy harvesting efficiency in GaN nanowire-based nanogenerators: the critical influence of the Schottky nanocontact. Nanoscale, 2017, 9, 4610-4619.	5.6	29
75	Effect of arsenic species on the kinetics of GaAs nanowires growth by molecular beam epitaxy. Journal of Crystal Growth, 2010, 312, 2073-2077.	1.5	27
76	Class-A dual-frequency VECSEL at telecom wavelength. Optics Letters, 2014, 39, 5586.	3.3	27
77	<i>In situ</i>passivation of GaAsP nanowires. Nanotechnology, 2017, 28, 495707.	2.6	27
78	Effect of nitrogen in the electronic structure of GaAsN and GaAsSb(N) compounds. Materials Science and Engineering C, 2002, 21, 251-254.	7.3	26
79	Subpicosecond pulse generation from a 156 â€‰Î¼m mode-locked VECSEL. Optics Letters, 2011, 36, 4377.	3.3	26
80	Growth and structural characterization of GaAs/GaAsSb axial heterostructured nanowires. Journal of Crystal Growth, 2009, 311, 1847-1850.	1.5	23
81	Growth of Inclined GaAs Nanowires by Molecular Beam Epitaxy: Theory and Experiment. Nanoscale Research Letters, 2010, 5, 1692-1697.	5.7	23
82	GaP/GaAs1âˆ’xPx nanowires fabricated with modulated fluxes: A step towards the realization of superlattices in a single nanowire. Journal of Crystal Growth, 2011, 323, 293-296.	1.5	23
83	GaN nanowires for piezoelectric generators. Physica Status Solidi - Rapid Research Letters, 2014, 8, 414-419.	2.4	23
84	Quasi one-dimensional transport in single GaAs/AlGaAs core-shell nanowires. Applied Physics Letters, 2011, 98, .	3.3	22
85	Spin-dependent photoconductivity in nonmagnetic semiconductors at room temperature. Applied Physics Letters, 2009, 95, .	3.3	21
86	Impact of the GaN nanowire polarity on energy harvesting. Applied Physics Letters, 2014, 104, .	3.3	20
87	Selective Area Growth of GaN Nanowires on Graphene Nanodots. Crystal Growth and Design, 2020, 20, 552-559.	3.0	20
88	The effect of potential fluctuations on the optical properties of InGaAsâˆ•InAlAs superlattices. Journal of Applied Physics, 2005, 97, 103518.	2.5	19
89	Floor free 10-Gb/s transmission with directly modulated GaInNAs-GaAs 1.35-/spl mu/m laser for metropolitan applications. IEEE Photonics Technology Letters, 2005, 17, 971-973.	2.5	19
90	Electroabsorption modulator based on Wannierâ€“Stark localization with 20 GHz/V efficiency. Applied Physics Letters, 1992, 61, 2773-2775.	3.3	18

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91	Band discontinuities inInxGa1â^'xAs-InP and InP-AlyIn1â^'yAs heterostructures:Evidence of noncommutativity. Physical Review B, 1997, 55, 2274-2279.	3.2	18
92	MBE growth of InAsN on (100) InAs substrates. Physica Status Solidi (B): Basic Research, 2005, 242, R43-R45.	1.5	18
93	Giant spin-dependent photo-conductivity in GaAsN dilute nitride semiconductor. Physical Review B, 2011, 83, .	3.2	18
94	Effect of nitrogen on the GaAs0.9â^'xNxSb0.1 dielectric function from the near-infrared to the ultraviolet. Applied Physics Letters, 2010, 97, 201903.	3.3	17
95	InP1â^'xAsx quantum dots in InP nanowires: A route for single photon emitters. Journal of Crystal Growth, 2013, 378, 519-523.	1.5	17
96	Ultrashort pulse generation from 156 Âµm mode-locked VECSEL at room temperature. Optics Express, 2010, 18, 19902.	3.4	16
97	Room-temperature optical manipulation of nuclear spin polarization in GaAsN. Physical Review B, 2014, 90, .	3.2	16
98	Ultrafast InGaAs/InGaAlAs multiple-quantum-well electro-absorption modulator for wavelength conversion at high bit rates. Applied Physics Letters, 2004, 84, 4268-4270.	3.3	15
99	Scaling of the saturation energy in microcavity saturable absorber devices. Applied Physics Letters, 2006, 88, 153513.	3.3	15
100	Cost-Effective Thermally-Managed 1.55-$mu{m m}$ VECSEL With Hybrid Mirror on Copper Substrate. IEEE Journal of Quantum Electronics, 2012, 48, 643-650.	1.9	15
101	Fabrication of an InGaAs spin filter by implantation of paramagnetic centers. Applied Physics Letters, 2013, 103, .	3.3	15
102	Band structure calculations for dilute nitride quantum wells under compressive or tensile strain. Journal of Physics Condensed Matter, 2004, 16, S3215-S3227.	1.8	14
103	Electron spin control in dilute nitride semiconductors. Journal of Physics Condensed Matter, 2009, 21, 174211.	1.8	14
104	Growth, structure and phase transitions of epitaxial nanowires of III-V semiconductors. Journal of Physics: Conference Series, 2010, 209, 012002.	0.4	14
105	Optical polarization properties of InAs/InP quantum dot and quantum rod nanowires. Nanotechnology, 2015, 26, 395701.	2.6	14
106	Morphology Tailoring and Growth Mechanism of Indium-Rich InGaN/GaN Axial Nanowire Heterostructures by Plasma-Assisted Molecular Beam Epitaxy. Crystal Growth and Design, 2018, 18, 2545-2554.	3.0	14
107	Nanoscale electrical analyses of axial-junction GaAsP nanowires for solar cell applications. Nanotechnology, 2020, 31, 145708.	2.6	14
108	Random stacking sequences in III-V nanowires are correlated. Physical Review B, 2014, 89, .	3.2	13

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109	Modeling, synthesis and study of highly efficient solar cells based on III-nitride nanowire arrays grown on Si substrates. Journal of Physics: Conference Series, 2015, 643, 012115.	0.4	13
110	GaN/Ga2O3 Core/Shell Nanowires Growth: Towards High Response Gas Sensors. Applied Sciences (Switzerland), 2019, 9, 3528.	2.5	13
111	Photoluminescence of an InAlAs/InGaAs Quantum Well Structure Grown on a GaAs Substrate. Japanese Journal of Applied Physics, 1990, 29, L233-L235.	1.5	12
112	InyGa1â^'yAs/InyAl1â^'yAs resonant tunneling diodes on GaAs. Applied Physics Letters, 1991, 59, 111-113.	3.3	11
113	Low power allâ€optical bistability in InGaAsâ€AlInAs superlattices: Demonstration of a wireless selfâ€electroâ€optical effect device operating at 1.5 Î¼m. Applied Physics Letters, 1994, 64, 742-744.	3.3	11
114	Si Incorporation in InP Nanowires Grown by Au-Assisted Molecular Beam Epitaxy. Journal of Nanomaterials, 2009, 2009, 1-7.	2.7	11
115	Effect of diffusion from a lateral surface on the rate of GaN nanowire growth. Semiconductors, 2012, 46, 838-841.	0.5	11
116	Photoluminescence study of interfaces between heavily doped Al0.48In0.52As:Si layers and InP (Fe) substrates. Journal of Applied Physics, 2002, 91, 8999-9004.	2.5	10
117	The effect of potential fluctuations on the optical properties of InGaAsâ^•InGaAlAs single and coupled double quantum wells. Journal of Applied Physics, 2006, 100, 053519.	2.5	10
118	Femtosecond pulse generation around 1500nm using a GaInNAsSb SESAM. Optics Express, 2008, 16, 18739.	3.4	10
119	Secondary ion mass spectrometry quantification of Be in AlxGa1â^'xAs/GaAs multilayer structures. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1988, 6, 2243-2247.	2.1	9
120	Investigation of low-power all-optical bistability in an InGaAs-InAs superlattice. Semiconductor Science and Technology, 1995, 10, 881-885.	2.0	9
121	Optimization and Characterization of InGaAsN/GaAs Quantum-well Ridge Laser Diodes for High Frequency Operation. Optical and Quantum Electronics, 2006, 38, 313-324.	3.3	9
122	Competition between confinement potential fluctuations and band-gap renormalization effects in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>In</mml:mtext></mml:mrow><mml:mrow><mml:mn>0.53</mml: Physical Review B, 2008, 77, .	3.2	9
123	Electron beam induced current microscopy investigation of GaN nanowire arrays grown on Si substrates. Materials Science in Semiconductor Processing, 2016, 55, 72-78.	4.0	9
124	Semiconductor quantum-wires and nano-wires for optoelectronic applications. Journal of Materials Science: Materials in Electronics, 2009, 20, 94-101.	2.2	8
125	Shiba Bound States across the Mobility Edge in Doped InAs Nanowires. Physical Review Letters, 2017, 119, 097701.	7.8	8
126	Statistics of Nucleation and Growth of Single Monolayers in Nanowires: Towards a Deterministic Regime. Physica Status Solidi - Rapid Research Letters, 2022, 16, .	2.4	8

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127	Highly thermally stable electrical compensation in oxygen implantedpâ€InAlAs. Applied Physics Letters, 1993, 62, 867-869.	3.3	7
128	Investigation of optical properties of interfaces between heavily doped Al0.48In0.52As:Si and InP (Fe) substrates by photoreflectance analysis. Journal of Applied Physics, 1999, 85, 4184-4188.	2.5	7
129	Clustering in GaAsSbN alloys as a possible origin of their atypical optical behavior: a Sb K-edge X-ray absorption study. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1931-1934.	0.8	7
130	Effects of repulsive and attractive ionized impurities on the resistivity of semiconductor heterostructures in the quantum Hall regime. Physical Review B, 2009, 80, .	3.2	7
131	In Situ X-ray Diffraction Study of GaN Nucleation on Transferred Graphene. Crystal Growth and Design, 2020, 20, 4013-4019.	3.0	7
132	Investigation of the effect of the doping order in GaN nanowire pâ€“n junctions grown by molecular-beam epitaxy. Nanotechnology, 2021, 32, 085705.	2.6	7
133	Shubnikov-de Haas - like oscillations in the vertical transport of semiconductor superlattices. Brazilian Journal of Physics, 1999, 29, 375-379.	1.4	7
134	InGaAs/InAlAs(Si) modulationâ€doped heterostructures intentionally lattice mismatched to InP substrates. Journal of Applied Physics, 1989, 66, 2633-2636.	2.5	6
135	Epitaxial growth and picosecond carrier dynamics of GaInAs/GaInNAs superlattices. Applied Physics Letters, 2009, 95, 141910.	3.3	6
136	Photoluminescence study of nitrogen effects on confined states in GaAs_{1â^’<i>x</i>}N_{<i>x</i>}GaAs quantum wells. EPJ Applied Physics, 2009, 47, 30302.	0.7	6
137	Magnetic thaw down and boil-off of electrons in the quantum Hall effect regime due to magnetoacceptors in GaAs/GaAlAs heterostructures. Physical Review B, 2012, 86, .	3.2	6
138	Phase coherent transport in GaAs/AlGaAs coreâ€“shellnanowires. Journal of Crystal Growth, 2013, 378, 546-548.	1.5	6
139	Class-A operation of an optically-pumped 16 Âµm-emitting quantum dash-based vertical-external-cavity surface-emitting laser on InP. Optics Express, 2017, 25, 11760.	3.4	6
140	Stable and high yield growth of GaP and In_{0.2}Ga_{0.8}As nanowire arrays using In as a catalyst. Nanoscale, 2020, 12, 18240-18248.	5.6	6
141	Quantitative Assessment of Carrier Density by Cathodoluminescence. I. GaAs Thin Films and Modeling. Physical Review Applied, 2021, 15, .	3.8	6
142	Dynamics of Droplet Consumption in Vaporâ€“Liquidâ€“Solid IIIâ€“V Nanowire Growth. Crystal Growth and Design, 2021, 21, 4647-4655.	3.0	6
143	Compatible laser emission and optical waveguide modulation at 1.5 Î¼m using Wannierâ€“Stark localization. Applied Physics Letters, 1992, 60, 1936-1938.	3.3	5
144	Potential-inserted InGaAs - AlGaInAs shallow quantum wells for electro-optical modulation at. Semiconductor Science and Technology, 1997, 12, 729-732.	2.0	5

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145	The Free Exciton Binding Energy in a Strained GaN0.02As0.98 Layer. AIP Conference Proceedings, 2005, , .	0.4	5
146	Photoluminescence properties of a Si doped InGaAs/InGaAlAs superlattice. Journal of Physics Condensed Matter, 2007, 19, 086207.	1.8	5
147	Effect of deposition conditions on nanowhisker morphology. Semiconductors, 2007, 41, 865-874.	0.5	5
148	Picosecond carrier lifetimes in dilute GaInNAs grown on InP substrate. Applied Physics Letters, 2011, 99, .	3.3	5
149	Crystallization of Si Templates of Controlled Shape, Size, and Orientation: Toward Micro- and Nanosubstrates. Crystal Growth and Design, 2015, 15, 2102-2109.	3.0	5
150	Importance of point defect reactions for the atomic-scale roughness of IIIâ€"V nanowire sidewalls. Nanotechnology, 2019, 30, 324002.	2.6	5
151	Investigation of GaN nanowires containing AlN/GaN multiple quantum discs by EBIC and CL techniques. Nanotechnology, 2019, 30, 214006.	2.6	5
152	Inâ€Situ Transmission Electron Microscopy Observation of Germanium Growth on Freestanding Graphene: Unfolding Mechanism of 3D Crystal Growth During Van der Waals Epitaxy. Small, 2022, 18, e2101890.	10.0	5
153	Regulated Dynamics with Two Monolayer Steps in Vaporâ€"Solidâ€"Solid Growth of Nanowires. ACS Nano, 2022, 16, 4397-4407.	14.6	5
154	Observation of the Wannier-Stark ladders associated to the light-hole ground state and to the heavy-hole first excited state in GaInAs/AlGaInAs superlattices. Nuovo Cimento Della Societa Italiana Di Fisica D - Condensed Matter, Atomic, Molecular and Chemical Physics, Biophysics, 1995, 17, 1763-1768.	0.4	4
155	Combined Raman study of InGaAsN from the N-impurity and InGaAs-matrix sides. Applied Physics Letters, 2007, 91, 051910.	3.3	4
156	Towards a monolithic optical cavity for atom detection and manipulation. European Physical Journal D, 2009, 53, 107-111.	1.3	4
157	Potential of semiconductor nanowires for single photon sources. Proceedings of SPIE, 2009, , .	0.8	4
158	Palladium assisted hetroepitaxial growth of an InAs nanowire by molecular beam epitaxy. Semiconductor Science and Technology, 2014, 29, 115005.	2.0	4
159	Influence of surface passivation on the electrical properties of pâ€"iâ€"n GaAsP nanowires. Applied Physics Letters, 2020, 117, 123104.	3.3	4
160	Quantitative Assessment of Carrier Density by Cathodoluminescence. II. GaAs Nanowires. Physical Review Applied, 2021, 15, .	3.8	4
161	Doping dependence of millimeterwave negative differential conductance in strain-compensated GaInAs/AlInAs superlattices. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 17, 294-296.	2.7	3
162	Continuous wave and time resolved spectroscopy of InAsN/GaAsN based quantum dots. Physica Status Solidi (A) Applications and Materials Science, 2005, 202, 2598-2603.	1.8	3

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163	Local structure of indium in quinary (InGa)(AsSbN)/GaAs quantum wells. Physical Review B, 2010, 82, .	3.2	3
164	Voltage bistability of coherent electron injection and nonlinear dynamics of a Bloch oscillation in a semiconductor superlattice. Physical Review B, 2015, 91, .	3.2	3
165	Growth Dynamics of Gallium Nanodroplets Driven by Thermally Activated Surface Diffusion. Journal of Physical Chemistry Letters, 2019, 10, 5082-5089.	4.6	3
166	Nucleation at the lateral surface and the shape of whisker nanocrystals. Semiconductors, 2007, 41, 1240-1247.	0.5	2
167	Optical constants and critical-point parameters of GaAs1-xSbxalloy films grown on GaAs. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 833-836.	1.8	2
168	Effects of temperature on transition energies of GaAsSbN/GaAs single quantum wells. Journal of Physics Condensed Matter, 2011, 23, 325801.	1.8	2
169	Magnetic two-dimensional field effect transistor. Applied Physics Letters, 2017, 111, .	3.3	2
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